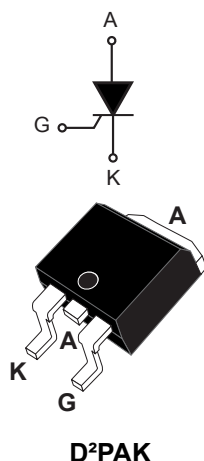


16 A 800 V high temperature SCR thyristor in D²PAK package



Features

- High junction temperature: $T_{jmax.} = 150\text{ }^{\circ}\text{C}$
- $V_{DRM} / V_{RRM} = 800\text{ V}$
- $V_{DSM} / V_{RSM} = 900\text{ V}$
- Tight I_{GT} spread: 5 to 8 mA
- High static immunity $dV/dt = 500\text{ V}/\mu\text{s}$ at $150\text{ }^{\circ}\text{C}$
- High turn-on rise $dI/dt = 100\text{ A}/\mu\text{s}$
- Halogen-free molding, lead-free plating
- ECOPACK2 compliant

Applications

- Inrush current limiting circuits in AC/DC converters
- General purpose AC line load switching
- Heating resistor control, solid state relays
- Crowbar and power bus discharge circuits

Description

Thanks to its operating junction temperature up to $150\text{ }^{\circ}\text{C}$, the **TN1605H-8G** offers high thermal performance operation up to 16 A rms in a D²PAK SMD package. Its trade-off noise immunity ($dV/dt = 500\text{ V}/\mu\text{s}$) versus its gate triggering current (maximum $I_{GT} = 8\text{ mA}$) and its turn-on current rise ($dI/dt = 100\text{ A}/\mu\text{s}$) allows to design robust and compact control circuit in AC/DC converters for inrush current limiting circuits and industrial drives, such as overvoltage crowbar protection, motor control circuits and power tools.

Product status

TN1605H-8G

Product summary

Order code	TN1605H-8G
Package	D ² PAK
$I_{T(RMS)}$	16 A
V_{DRM}/V_{RRM}	800 V
$T_j\text{ max.}$	$150\text{ }^{\circ}\text{C}$

1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

Symbol	Parameter		Value	Unit
I _{T(RMS)}	RMS on-state current (180° conduction angle)		T _C = 134 °C 16	A
I _{T(AV)}	Average on-state current (180 ° conduction angle)		T _C = 134 °C 10	A
			T _C = 139 °C 8	
			T _C = 142 °C 6	
I _{TSM}	Non repetitive surge peak on-state current (T _j initial = 25 °C)		t _p = 8.3 ms 177	A
			t _p = 10 ms 160	
I ² t	I ² t value for fusing		t _p = 10 ms 128	A ² s
V _{DRM} , V _{RRM}	Repetitive peak off-state voltage		800	V
V _{DSM} , V _{RSM}	Non repetitive peak off-state voltage		t _p = 10 ms V _{DRM} / V _{RRM} + 100 V	V
di/dt	Critical rate of rise of on-state current I _G = 2 x I _{GT} , t _r < 100 ns		f = 60 Hz 100	A/μs
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C 4	A
P _{G(AV)}	Average peak gate power dissipation		T _j = 150 °C 1	W
V _{RGM}	Maximum peak reverse gate voltage		5	V
T _{stg}	Storage junction temperature range		-40 to +150	°C
T _j	Operating junction temperature range		-40 to +150	
T _l	Maximum lead temperature soldering during 10 s		260	

Table 2. Electrical characteristics ($T_J = 25\text{ °C}$ unless otherwise specified)

Symbol	Test conditions			Value	Unit
I _{GT}	V _D = 12 V, R _L = 33 Ω		Min.	5	mA
V _{GT}			Max.	8	
				1.3	V
V _{GD}	V _D = V _{DRM} , R _L = 3.3 kΩ	T _j = 150 °C	Min.	0.2	V
I _H	I _T = 500 mA, gate open		Max.	30	mA
I _L	I _G = 1.2 x I _{GT} max.		Max.	40	mA
dV/dt	V _{OUT} = 536 V, gate open	T _j = 150 °C	Min.	500	V/μs
t _{gt}	I _T = 32 A, V _D = 536 V, I _G = 12 mA, (dI _G /dt) max = 0.2 A/μs		Typ.	1.9	μs
t _q	I _T = 32 A, V _D = 536 V, V _R = 25 V, dV _D /dt = 40 V/μs	T _j = 25 °C	Typ.	25	μs
		T _j = 150 °C	Typ.	85	μs

Table 3. Static characteristics

Symbol	Test conditions			Value	Unit
V_{TM}	$I_{TM} = 32\text{ A}$, $t_p = 380\text{ }\mu\text{s}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	1.55	V
V_{TO}	Threshold voltage	$T_j = 150\text{ }^\circ\text{C}$	Max.	0.82	
R_D	Dynamic resistance	$T_j = 150\text{ }^\circ\text{C}$	Max.	25	m Ω
I_{DRM} , I_{RRM}	$V_D = V_{DRM}$; $V_R = V_{RRM}$	$T_j = 25\text{ }^\circ\text{C}$	Max.	1	μA
		$T_j = 150\text{ }^\circ\text{C}$		3.5	mA

Table 4. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	Max.	1.1	$^\circ\text{C/W}$
$R_{th(j-a)}$	Junction to ambient, $S = 2.5\text{ cm}^2$ ⁽¹⁾ , $e_{CU} = 70\text{ }\mu\text{m}$	Typ.	45	

1. Copper surface under tab, on PCB FR4

1.1 Characteristics curves

Figure 1. Maximum average power dissipation versus average on-state current

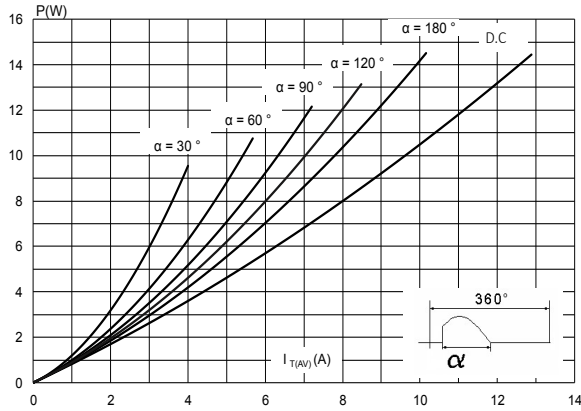


Figure 2. Average and DC on-state current versus case temperature

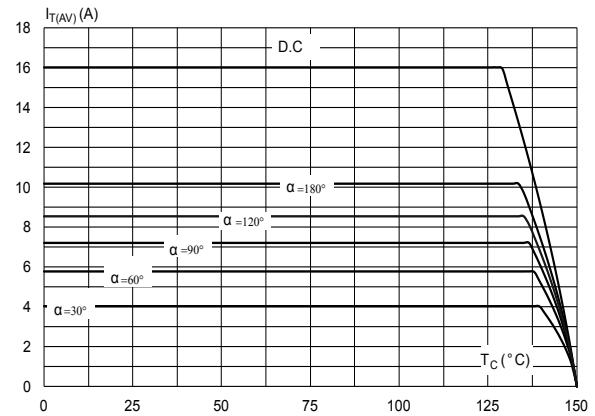


Figure 3. Average and D.C. on-state current versus ambient temperature

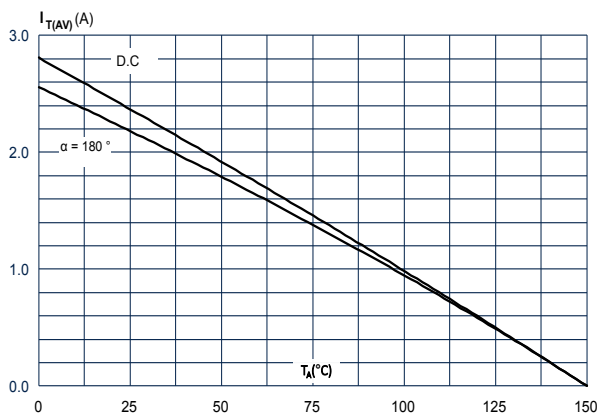


Figure 4. On-state characteristics (maximum values)

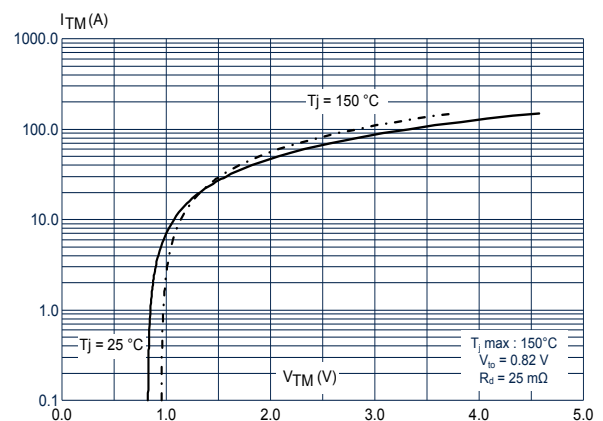


Figure 5. Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration

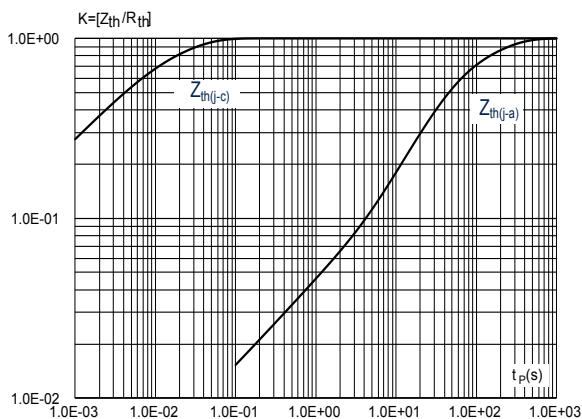


Figure 6. Surge peak on-state current versus number of cycles

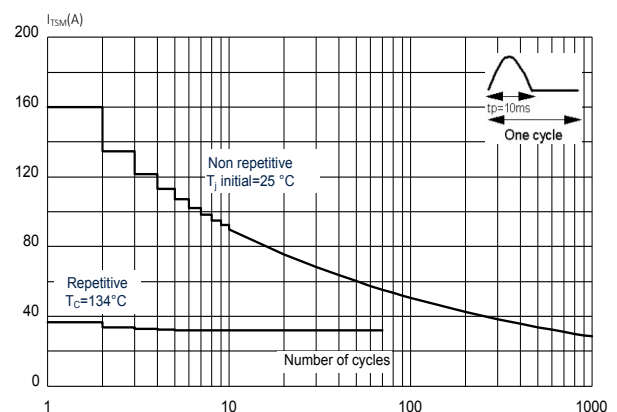


Figure 7. Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms

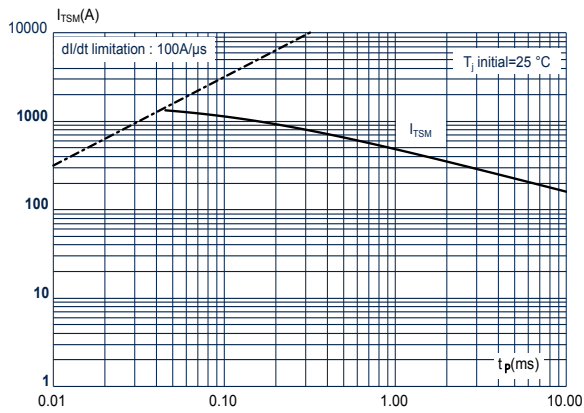


Figure 8. Relative variation of holding current and latching current versus junction temperature (typical values)

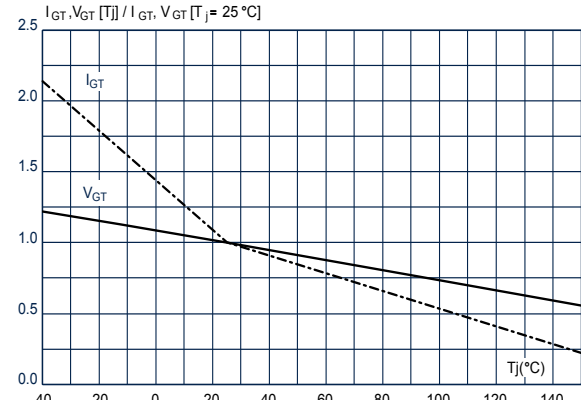


Figure 9. Relative variation of gate triggering current and voltage versus junction temperature (typical values)

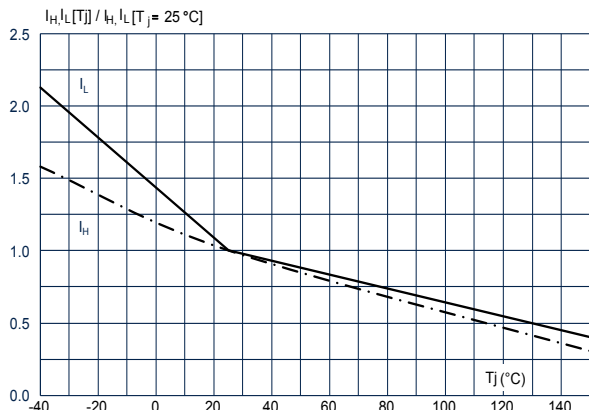


Figure 10. Relative variation of static dV/dt immunity versus junction temperature (typical values)

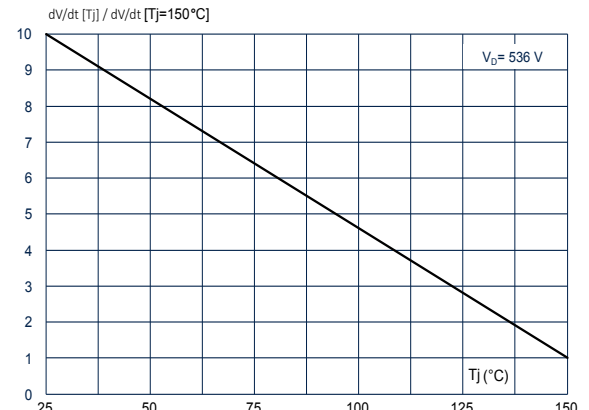


Figure 11. Relative variation of leakage current versus junction temperature for 800 V blocking voltage

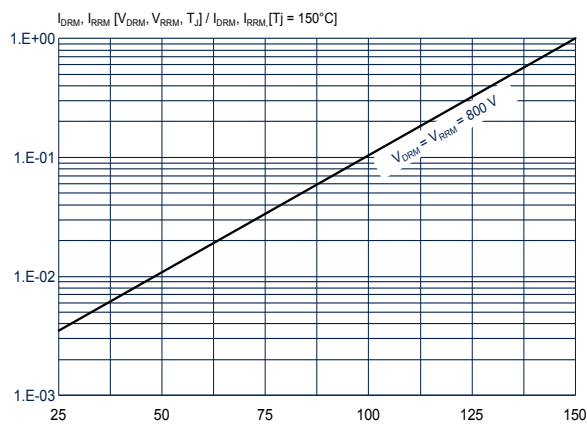
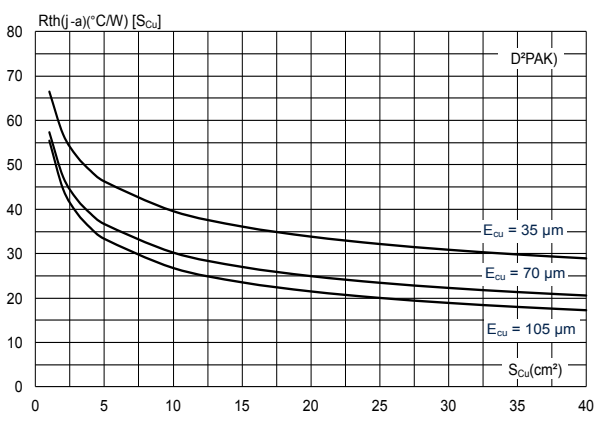


Figure 12. Thermal resistance junction to ambient versus copper surface under tab



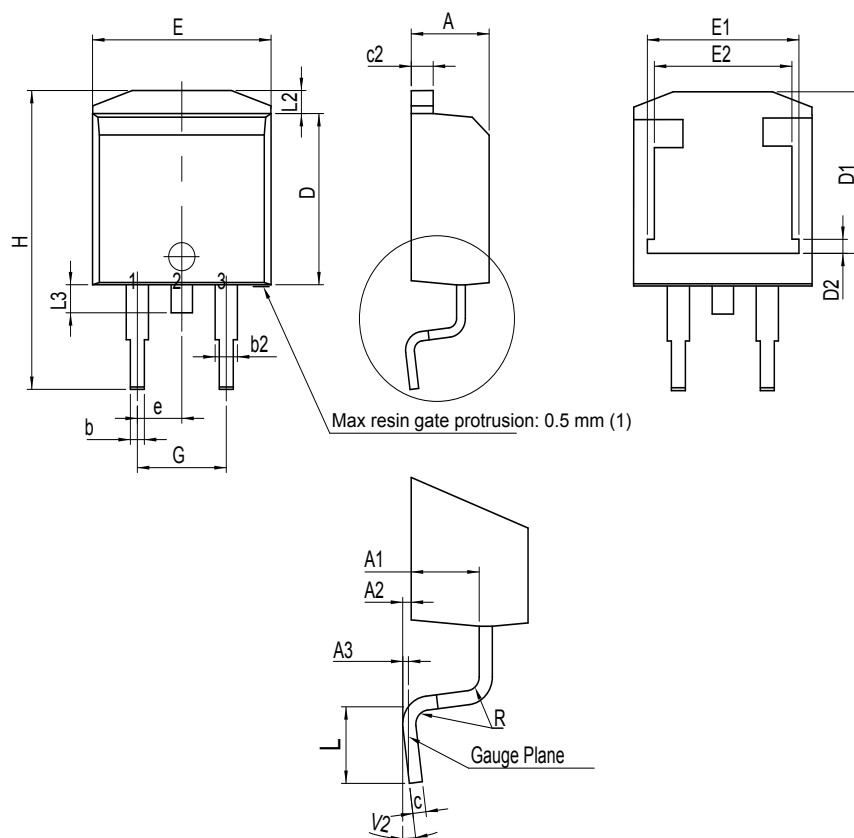
2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 D²PAK package information

- **ECOPACK2** compliant
- Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL94 flammability standard level V0

Figure 13. D²PAK package outline



(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

Table 5. D²PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
e	2.54			0.10000		
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.19		1.40	0.0468		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2 ⁽²⁾	0°		8°	0°		8°

1. Dimensions in inches are given for reference only

2. Degrees

Figure 14. D²PAK recommended footprint (dimensions are in mm)

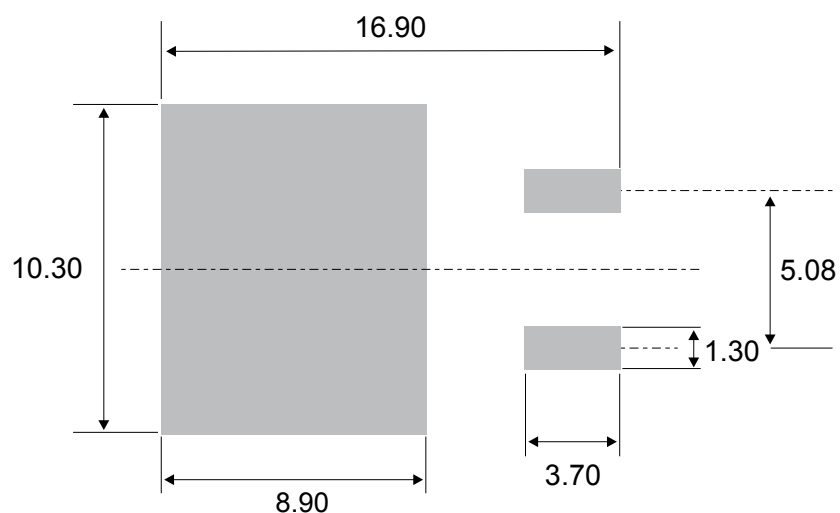
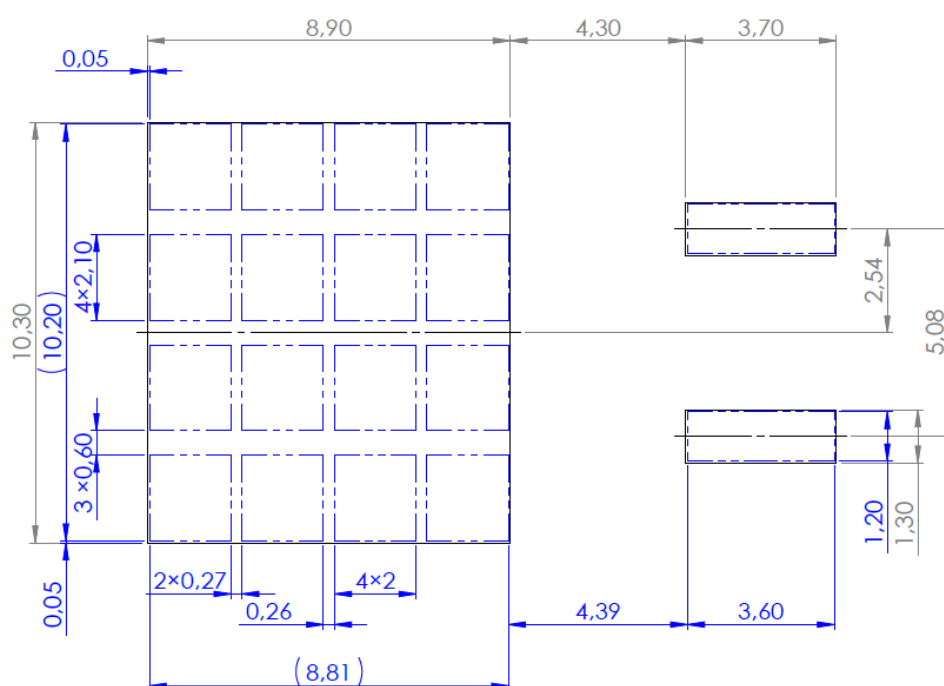


Figure 15. D²PAK stencil definitions (dimensions are in mm)



3 Ordering information

Figure 16. Ordering information scheme

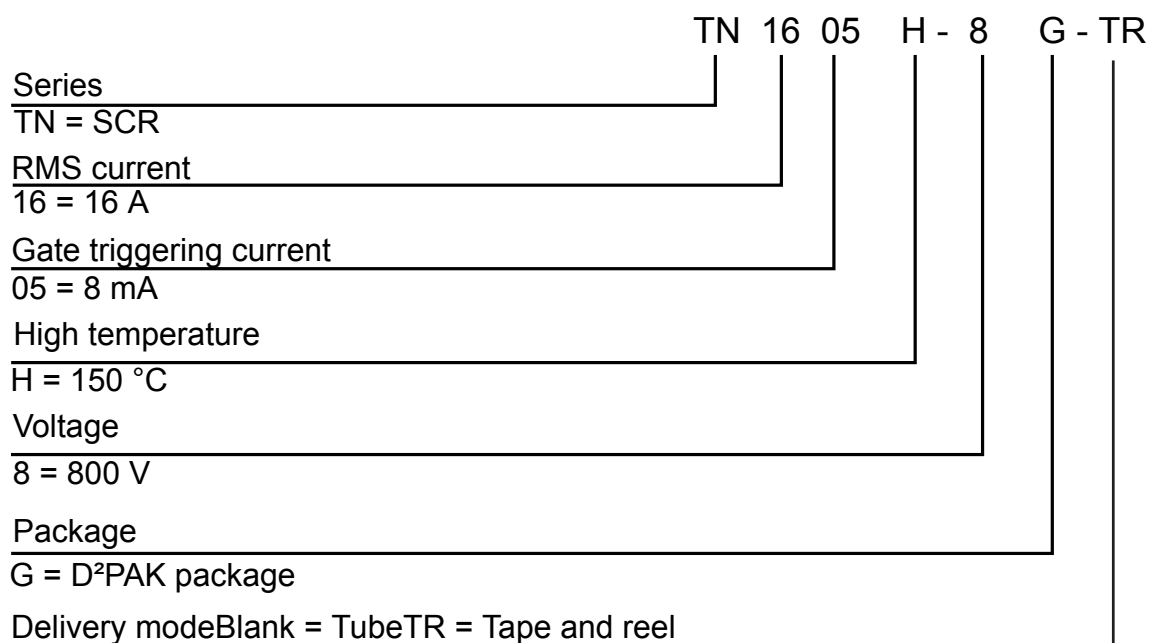


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN1605H-8G	TN1605H8G	D ² PAK	1.5 g	50	Tube
TN1605H-8G-TR				1000	Tape and reel

Revision history

Table 7. Document revision history

Date	Revision	Changes
05-Dec-2022	1	Initial release.

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